

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-15 (Canceled)

Claim 16 (currently amended): A semiconductor device comprising:

first and second wells opposite in conductivity types and disposed adjacent to each other;
a well isolation structure comprising a shallow trench formed on a boundary of said first and second wells;

a first device region provided in said first well;

a second device region provided in said second well, said first and second device regions being disposed to oppose each other face-to-face, with said well isolation structure disposed between said first and second device regions;

a third device region provided in said first well, said third device region being provided separately from said first device region;

a fourth device region provided in said second well, said third and fourth device regions being disposed not to oppose each other face-to-face, with said well isolation structure disposed between said third and fourth device regions, said fourth device region being provided separately from said second device region;

wherein a first width of said well isolation structure between said first and second device regions is smaller than a second width of said well isolation structure between said third and fourth device regions.

Claim 17 (previously presented): The semiconductor device according to claim 16, wherein said first, second, third and fourth device regions have substantially same configuration.

Claim 18 (currently amended): A semiconductor device comprising:

a first well of p type and a second well of n type disposed adjacent to each other;

a well isolation structure comprising a shallow trench formed on a boundary of said first and second wells;

a pair of a first device region of n type and a second device region of p type, said first and second device regions being disposed to oppose each other face-to-face, with said well isolation structure disposed between said first device region and said second device region;

a third device region of n type and fourth device region of p type, said third and fourth device regions being disposed not to oppose each other face-to-face, with said well isolation structure disposed between said third device region and said fourth device region;

wherein said first and third device regions are separately provided in said first well and said third and fourth device regions are separately provided in said second well, and a first width of said well isolation structure between said first and second device regions is smaller than a second width of said well isolation structure between said third and fourth device regions.